# Atsushi Nishikawa

List of Publications by Year
in descending order



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|---|---|---|---|
| 45 papers | 692 citations | 759233 12 h-index | 713466 21 g-index |
| 45 all docs | 45 docs citations | 45 times ranked | 441 citing authors |

| # | Article | IF | Citations |
| --- | --- | --- | --- |
| 1 | Investigation of optical gain in Eu-doped GaN thin film grown by OMVPE method. Journal of Science: Advanced Materials and Devices, 2016, 1, 220-223. | 3.1 | 7 |
| 2 | In situ Eu doping into Al Ga1â^'N grown by organometallic vapor phase epitaxy to improve luminescence properties. Optical Materials, 2015, 41, 75-79. | 3.6 | 8 |
| 3 | Excellent uniformity on large diameter GaN on silicon LED wafer. Physica Status Solidi C: Current Topics in Solid State Physics, 2014, 11, 624-627. | 0.8 | 5 |
| 4 | GaN-on-Si wafers for HEMTs with high power-driving capability. Physica Status Solidi C: Current Topics in Solid State Physics, 2014, 11, 945-948. | 0.8 | 5 |
| 5 | Defect roles in the excitation of Eu ions in Eu:GaN. Optics Express, 2013, 21, 30633. | 3.4 | 9 |
| 6 | Highly Uniform Electroluminescence from 150 and 200 mm GaN-on-Si-Based Blue Light-Emitting Diode Wafers. Applied Physics Express, 2013, 6, 095502. | 2.4 | 7 |
| 7 | 200-mm GaN-on-Si Based Blue Light-Emitting Diode Wafer with High Emission Uniformity. Japanese Journal of Applied Physics, 2013, 52, 08JB25. | 1.5 | 9 |
| 8 | Dislocation generation in GaN by dicing process. Journal of Physics: Conference Series, 2013, 417, 012055. | 0.4 | 1 |
| 9 | Advanced Materials Design of Rare-Earth-Doped Semiconductors by Organometallic Vapor Phase Epitaxy. , 2013, , 261-272. | | 0 |
| 10 | Eu luminescence center created by Mg codoping in Eu-doped GaN. Applied Physics Letters, 2012, 100, . | 3.3 | 50 |
| 11 | Fluorescence XAFS Analysis of Eu-Doped GaN Layers Grown by Organometallic Vapor Phase Epitaxy. E-Journal of Surface Science and Nanotechnology, 2011, 9, 51-53. | 0.4 | 6 |
| 12 | Atmospheric pressure growth of Euâ€doped GaN by organometallic vapor phase epitaxy. Physica Status Solidi (A) Applications and Materials Science, 2011, 208, 445-448. | 1.8 | 10 |
| 13 | Site and sample dependent electronâ€“phonon coupling of Eu ions in epitaxial-grown GaN layers. Optical Materials, 2011, 33, 1050-1054. | 3.6 | 48 |
| 14 | Room-temperature red emission from light-emitting diodes with Eu-doped GaN grown by organometallic vapor phase epitaxy. Optical Materials, 2011, 33, 1071-1074. | 3.6 | 23 |
| 15 | Site Selective Magneto-Optical Studies of Eu ions in Gallium Nitride. Materials Research Society Symposia Proceedings, 2011, 1342, 93. | 0.1 | 3 |
| 16 | Electroluminescence Properties of Eu-doped GaN-based Light-emitting Diodes Grown by Organometallic Vapor Phase Epitaxy. Materials Research Society Symposia Proceedings, 2011, 1342, 27. | 0.1 | 15 |
| 17 | Nature and Excitation Mechanism of the Emission-dominating Minority Eu-center in GaN Grown by Organometallic Vapor-phase Epitaxy. Materials Research Society Symposia Proceedings, 2011, 1342, 67. | 0.1 | 4 |
| 18 | Electroluminescence properties of Eu-doped GaN-based red light-emitting diode by OMVPE. Physica Status Solidi (A) Applications and Materials Science, 2010, 207, 1397-1399. | 1.8 | 19 |

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|---|---|---|---|
| 19 | Effect of growth temperature on Eu-doped GaN layers grown by organometallic vapor phase epitaxy. Physica Status Solidi C: Current Topics in Solid State Physics, 2010, 7, 2040-2042. | 0.8 | 12 |
| 20 | Lattice site location of optical centers in GaN:Eu light emitting diode material grown by organometallic vapor phase epitaxy. Applied Physics Letters, 2010, 97, 111911. | 3.3 | 29 |
| 21 | Improved Eu Luminescence Properties in Eu-Doped GaN Grown on GaN Substrates by Organometallic Vapor Phase Epitaxy. Japanese Journal of Applied Physics, 2010, 49, 048001. | 1.5 | 2 |
| 22 | Growth Temperature Dependence of Eu-Doped GaN Grown by Organometallic Vapor Phase Epitaxy. Zairyo/Journal of the Society of Materials Science, Japan, 2010, 59, 671-674. | 0.2 | 0 |
| 23 | Efficient luminescence from rare-earth elements by nitride-based nano-particle. Hosokawa Powder Technology Foundation ANNUAL REPORT, 2010, 18, 38-44. | 0.0 | 0 |
| 24 | Low-temperature characteristics of the current gain of GaN/InGaN double-heterojunction bipolar transistors. Journal of Crystal Growth, 2009, 311, 3000-3002. | 1.5 | 2 |
| 25 | Development of new-type 1.5 Î¼m light-emitting devices based on Er,O-codoped GaAs. Journal of Physics: Conference Series, 2009, 165, 012025. | 0.4 | 2 |
| 26 | High-temperature (300 Â°C) operation ofnpn-type GaN/InGaN double heterojunction bipolar transistors. Physica Status Solidi C: Current Topics in Solid State Physics, 2008, 5, 2957-2959. | 0.8 | 1 |
| 27 | High-Temperature Characteristics of Al<sub>x</sub>Ga<sub>1-x</sub>N-Based Vertical Conducting Diodes. Japanese Journal of Applied Physics, 2008, 47, 2838. | 1.5 | 2 |
| 28 | Temperature dependence of current-voltage characteristics of npn-type GaNâˆ•InGaN double heterojunction bipolar transistors. Applied Physics Letters, 2007, 91, 133514. | 3.3 | 7 |
| 29 | High Critical Electric Field Exceeding 8 MV/cm Measured Using an AlGaNpâ€"iâ€"nVertical Conducting Diode onn-SiC Substrate. Japanese Journal of Applied Physics, 2007, 46, 2316-2319. | 1.5 | 32 |
| 30 | Low-resistance graded AlxGa1âˆ'xN buffer layers for vertical conducting devices on n-SiC substrates. Journal of Crystal Growth, 2007, 298, 819-821. | 1.5 | 2 |
| 31 | Low on-resistance of GaNp-i-n vertical conducting diodes grown on 4H-SiC substrates. Physica Status Solidi C: Current Topics in Solid State Physics, 2007, 4, 2662-2665. | 0.8 | 4 |
| 32 | High breakdown field of pnp GaN/InGaN/AlGaN DHBTs with AlGaN collector. Physica Status Solidi (A) Applications and Materials Science, 2007, 204, 2037-2041. | 1.8 | 3 |
| 33 | Growth and optical characterization of InAsN quantum dots. Physica Status Solidi (B): Basic Research, 2006, 243, 1657-1660. | 1.5 | 11 |
| 34 | Critical electric fields of AlGaN in AlGaN-based vertical conducting diodes on -SiC substrates. Superlattices and Microstructures, 2006, 40, 332-337. | 3.1 | 9 |
| 35 | p-InGaN/n-GaN Vertical Conducting Diodes onn+-SiC Substrate for High Power Electronic Device Applications. Japanese Journal of Applied Physics, 2006, 45, 3387-3390. | 1.5 | 2 |
| 36 | High critical electric field of AlxGa1âˆ'xN p-i-n vertical conducting diodes on n-SiC substrates. Applied Physics Letters, 2006, 88, 173508. | 3.3 | 29 |

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|---|---|---|---|
| 37 | High breakdown voltage with low on-state resistance of p-InGaNâˆ•n-GaN vertical conducting diodes on n-GaN substrates. Applied Physics Letters, 2006, 89, 153509. | 3.3 | 4 |
| 38 | Excitation power dependent photoluminescence of In0.7Ga0.3As1âˆ’xNx quantum dots grown on GaAs (001). Journal of Crystal Growth, 2005, 278, 244-248. | 1.5 | 7 |
| 39 | Growth and characterization of InAsN alloy films and quantum wells. Journal of Crystal Growth, 2005, 278, 254-258. | 1.5 | 33 |
| 40 | Current-voltage characteristics of pâ€InGaNâˆ•nâ€GaN vertical conducting diodes on n+â€SiC substrates. Applied Physics Letters, 2005, 87, 233505. | 3.3 | 11 |
| 41 | MBE growth and photoreflectance study of GaAsN alloy films grown on GaAs (001). Journal of Crystal Growth, 2003, 251, 427-431. | 1.5 | 23 |
| 42 | RF-MBE growth of InAsN layers on GaAs (001) substrates using a thick InAs buffer layer. Journal of Crystal Growth, 2003, 251, 422-426. | 1.5 | 12 |
| 43 | The effect of nitrogen on self-assembled GaInNAs quantum dots grown on GaAs. Physica Status Solidi (B): Basic Research, 2003, 240, 310-313. | 1.5 | 9 |
| 44 | Effect of nitrogen on the optical and transport properties of Ga0.48In0.52NyP1âˆ’y grown on GaAs(001) substrates. Applied Physics Letters, 2003, 83, 5446-5448. | 3.3 | 32 |
| 45 | Room-Temperature Red Emission from a p-Type/Europium-Doped/n-Type Gallium Nitride Light-Emitting Diode under Current Injection. Applied Physics Express, 0, 2, 071004. | 2.4 | 183 |